

03500.017757.



IFW

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
HIDEYA KUMONI : Examiner: Not Yet Assigned  
Application No.: 10/535,196 ) Group Art Unit: 1765  
Filed: May 18, 2005 )  
For: PROCESS FOR PRODUCING )  
CRYSTALLINE THIN FILM : September 20, 2006

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

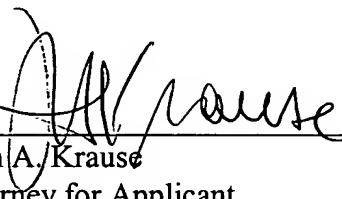
In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed articles and non-U.S. documents are also enclosed.

For the concise explanation of relevance of non-English document JP 3204986, the Examiner is referred to the English language counterparts U.S. Pat Appl. Nos. 2001-0001745 A1, 2003/0096489 A1, 2003/0119286 A1 and 2005/0255640 A1. The Examiner is also referred to U.S. Pat Nos. 6,555,449 B1, 6,322,625 B2 and 7,029,996 B2.

It is respectfully requested that the above information be considered by the Examiner and that an initialed copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicant's undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address given below.

Respectfully submitted,

  
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U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)  
(Use several sheets if necessary)

SEP 21 2006

APPLICANT

HIDEYA KUMONI

FILING DATE

May 18, 2005

GROUP

1765

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	2001/0001745 A1	05/24/01	Im et al.	438	747	
	2003/0096489 A1	05/22/03	Im et al.	438	487	
	2003/0119286 A1	06/26/03	Im et al.	438	487	
	2005/0255640 A1	11/17/05	Im et al.	438	166	
	2006/0177361	08/10/06	Kumomi	422	245.1	
	6,555,449 B1	04/29/03	Im et al.	438	487	
	6,322,625 B2	11/27/01	Im	117	43	
	7,029,996 B2	04/18/06	Im et al	438	487	

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
JP	3204986	06/29/01	Japan			US 2001/0001745 A1 US 2003/0096489 A1 US 2003/0119286 A1 US 2005/0255640 A1 US 6,555,449 B1 US 6,322,625 B2 US 7,029,996 B2

## OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

	A. Hara et al. "High-Performance Polycrystalline Silicon Thin Film Transistors on Non-Alkali Glass Produced Using Continuous Wave Laser Lateral Crystallization", Jpn. J. Appl. Phys., Vol. 41 Part 2, pp. L311-L313 (2002).
	A. Hara et al. "Large Grain Poly-Si TFTs by Scanning CW Laser Crystallization", AM-LCD '02 Digest of Tech. Paper, pp. 227-230 (2002).
	M. Tai et al. "Performance of Low Temperature Poly-Si TFTs Fabricated by Selectively Enlarging Laser Crystallization (SELAX)", AM-LCD '02 Digest of Tech. Paper, pp. 231-234 (2002).
	R. Sposili et al. "Sequential Lateral Solidification of Thin Silicon Films on SiO <sub>2</sub> ", Appl. Phys. Lett., Vol. 69 No. 19, pp. 2864-2866 (1996).
	Jin Song H. Et al. "Single-crystal Si Islands on SiO <sub>2</sub> Obtained via Excimer-laser Irradiation of A Patterned Si Film", Appl. Phys. Lett., Vol. 68 No. 22, pp. 3165-3167 (1996).

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 1